IXYS

Preliminary Technical Information

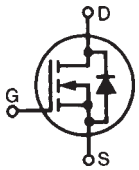
PolarHV™HiPerFET Power MOSFET

(Electrically Isolated Tab)

IXFP 8N50PM

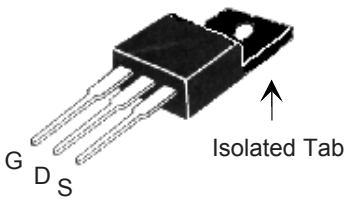
V_{DSS} = 500 V
I_{D25} = 4.4 A
$R_{DS(on)}$ ≤ 0.8 Ω
trr ≤ 200 ns

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode



Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	500	V
V_{DGR}	T_J = 25°C to 150°C; R_{GS} = 1 MΩ	500	V
V_{GS}	Continuous	±30	V
V_{GSM}	Transient	±40	V
I_{D25}	T_C = 25°C	4.4	A
I_{DM}	T_C = 25°C, pulse width limited by T_{JM}	14	A
I_{AR}	T_C = 25°C	8	A
E_{AR}	T_C = 25°C	20	mJ
E_{AS}	T_C = 25°C	300	mJ
dv/dt	$I_S \le I_{DM}$, di/dt ≤100 A/μs, $V_{DD} \le V_{DSS}$, T_J ≤150°C, R_G = 18 Ω	10	V/ns
P_D	T_C = 25°C	42	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	1.6 mm (0.062 in.) from case for 10 s	300	°C
T_{SOLD}	Plastic body for 10 s	260	°C
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight		4	g

OVERMOLDED TO-220 (IXTP...M) OUTLINE



G = Gate D = Drain
S = Source

Symbol (T_J = 25°C unless otherwise specified)	Test Conditions	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0 V, I_D = 250 μA	500			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 1 mA	3.0		5.5	V
I_{GSS}	V_{GS} = ±30 V_{DC}, V_{DS} = 0			±100	nA
I_{DSS}	$V_{DS} = V_{DSS}$, V_{GS} = 0 V			5	μA
	T_J = 125°C			500	μA
$R_{DS(on)}$	V_{GS} = 10 V, I_D = 4 A Pulse test, t ≤300 μs, duty cycle d ≤ 2 %			0.8	Ω

Features

- Plastic overmolded tab for electrical isolation
- International standard package
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
  - easy to drive and to protect
- Fast Intrinsic Diode

Advantages

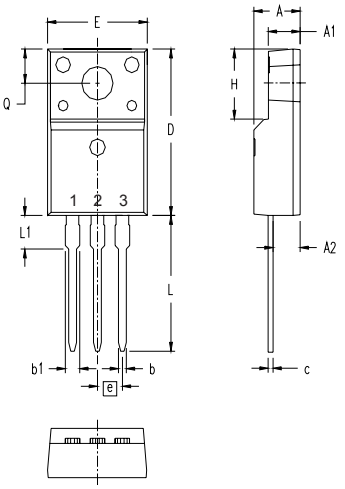
- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values (T_J = 25° C unless otherwise specified) Min.	Typ.	Max.	
g_{fs}	V_{DS}= 10 V; I_D = 4 A	5	8		S
C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		1050		pF
C_{oss}			120		pF
C_{rss}			12		pF
$t_{d(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 V_{DSS}, I_D = 8 A R_G = 18 Ω (External)		22		ns
t_r			28		ns
$t_{d(off)}$			65		ns
t_f			23		ns
$Q_{g(on)}$	V_{GS}= 10 V, V_{DS} = 0.5 V_{DSS}, I_D = 4 A		20		nC
Q_{gs}			7		nC
Q_{gd}			7		nC
R_{thJS}				3.0	°C/W

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values (T_J = 25° C, unless otherwise specified) Min.	Typ.	Max.	
I_S	V_{GS} = 0 V			8	A
I_{SM}	Repetitive			14	A
V_{SD}	I_F = I_S, V_{GS} = 0 V, Pulse test, t ≤300 μs, duty cycle d≤ 2 %			1.5	V
t_{rr}	I_F = 8 A, V_{GS}=0V, V_R=100V -di/dt = 100 A/μs			200	ns
Q_{RM}			0.25		μC
I_{RM}			2		A

ISOLATED TO-220 (IXTP...M)



Terminals: 1 - Gate
2 - Drain (Collector)
3 - Source (Emitter)

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.177	.193	4.50	4.90
A1	.092	.108	2.34	2.74
A2	.101	.117	2.56	2.96
b	.028	.035	0.70	0.90
b1	.050	.058	1.27	1.47
c	.018	.024	0.45	0.60
D	.617	.633	15.67	16.07
E	.392	.408	9.96	10.36
e	.100 BSC		2.54 BSC	
H	.255	.271	6.48	6.88
L	.499	.523	12.68	13.28
L1	.119	.135	3.03	3.43
ØP	.121	.129	3.08	3.28
Q	.126	.134	3.20	3.40

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.